

10/709,869

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("5770484").PN.	USPAT	OR	OFF	2005/04/18 14:31
L2	1	("5981332").PN.	USPAT	OR	OFF	2005/04/18 14:31
L3	1	("5945704").PN.	USPAT	OR	OFF	2005/04/18 14:32
L4	334	438/311	USPAT	OR	ON	2005/04/18 14:32
L5	1128	438/243	USPAT	OR	ON	2005/04/18 14:32
L6	1044	438/386	USPAT	OR	ON	2005/04/18 14:32
L7	286	438/431	USPAT	OR	ON	2005/04/18 14:32
L8	300	438/433	USPAT	OR	ON	2005/04/18 14:32
L9	3094	438/637	USPAT	OR	ON	2005/04/18 14:33
L10	1216	438/638	USPAT	OR	ON	2005/04/18 14:33
L11	964	438/639	USPAT	OR	ON	2005/04/18 14:33
L12	1360	438/643	USPAT	OR	ON	2005/04/18 14:33
L13	1128	438/680	USPAT	OR	ON	2005/04/18 14:33
L14	1460	438/700	USPAT	OR	ON	2005/04/18 14:33
L15	836	438/712	USPAT	OR	ON	2005/04/18 14:33
L16	746	438/770	USPAT	OR	ON	2005/04/18 14:33
L17	68	438/914	USPAT	OR	ON	2005/04/18 14:36
L18	1	("6316310").PN.	USPAT	OR	OFF	2005/04/18 14:36
L19	1	("6218319").PN.	USPAT	OR	OFF	2005/04/18 14:36
L20	1	18 and (dopant or source or portion or lower or upper or trench or side or wall or RIE or temperature or thickness or liner or cap or nitride or oxide or silicon or oxidation or thermal or cvd or lpcvd or doping or doped or lower or upper or portion or preventing)	USPAT	OR	ON	2005/04/18 14:48
L21	1	19 and (dopant or source or portion or lower or upper or trench or side or wall or RIE or temperature or thickness or liner or cap or nitride or oxide or silicon or oxidation or thermal or cvd or lpcvd or doping or doped or lower or upper or portion or preventing)	USPAT	OR	ON	2005/04/18 14:40
L22	1	3 and (dopant or source or portion or lower or upper or trench or side or wall or RIE or temperature or thickness or liner or cap or nitride or oxide or silicon or oxidation or thermal or cvd or lpcvd or doping or doped or lower or upper or portion or preventing)	USPAT	OR	ON	2005/04/18 14:49

L23	1	2 and (dopant or source or portion or lower or upper or trench or side or wall or RIE or temperature or thickness or liner or cap or nitride or oxide or silicon or oxidation or thermal or cvd or lpcvd or doping or doped or lower or upper or portion or preventing)	USPAT	OR	ON	2005/04/18 14:55
L24	1	1 and (dopant or source or portion or lower or upper or trench or side or wall or RIE or temperature or thickness or liner or cap or nitride or oxide or silicon or oxidation or thermal or cvd or lpcvd or doping or doped or lower or upper or portion or preventing)	USPAT	OR	ON	2005/04/18 14:55
S1	752	EPROM and floating and control and gate and doped and source and drain and region and channel and n-type and p-type and polysilicon	USPAT	OR	ON	2005/04/02 09:17
S2	0	EPROM and floating and control and gate and doped and source and drain and region and channel and n-type and p-type and polysilicon and (polysilicon adj floating adj electrode)	USPAT	OR	ON	2005/04/02 09:18
S3	23	EPROM and floating and control and gate and doped and source and drain and region and channel and n-type and p-type and polysilicon and electrode and (tunnel adj oxide) and negative and positive and voltage and transistor and band	USPAT	OR	ON	2005/04/02 09:20
S4	0	EPROM and floating and control and gate and doped and source and drain and region and channel and n-type and p-type and polysilicon and electrode and (tunnel adj oxide) and negative and positive and voltage and transistor and band and (doped adj polysilicon)	USPAT	OR	ON	2005/04/02 09:20
S5	5	EPROM and floating and control and gate and doped and source and drain and region and channel and n-type and p-type and polysilicon and electrode and (tunnel adj oxide) and negative and positive and voltage and transistor and band and (doped adj polysilicon)	USPAT	OR	ON	2005/04/02 09:42

S6	1	("5761125").PN.	USPAT	OR	OFF	2005/04/02 09:44
S7	53	trench and sidewall and dopant and source and collar and liner and (buried adj plate)	USPAT	OR	ON	2005/04/18 12:16
S8	19	S7 and oxide and nitride and silicon and ASG	USPAT	OR	ON	2005/04/18 12:27
S9	19	S8 and (dopant or source or portion or lower or upper or trench or side or wall or RIE or temperature or thickness or liner or cap or nitride or oxide or silicon or oxidation or thermal)	USPAT	OR	ON	2005/04/18 14:37